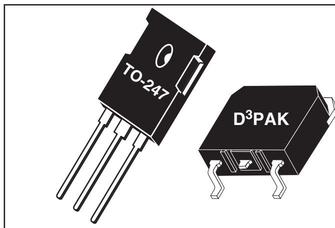
APT7F120B
APT7F120S

1200V, 7A, 2.4Ω Max, t_{rr} ≤190ns

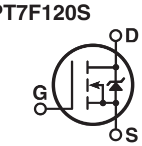
N-Channel FREDFET

Power MOS 8™ is a high speed, high voltage N-channel switch-mode power MOSFET. This 'FREDFET' version has a drain-source (body) diode that has been optimized for high reliability in ZVS phase shifted bridge and other circuits through reduced t_{rr}, soft recovery, and high recovery dv/dt capability. Low gate charge, high gain, and a greatly reduced ratio of C_{rss}/C_{iss} result in excellent noise immunity and low switching loss. The intrinsic gate resistance and capacitance of the poly-silicon gate structure help control di/dt during switching, resulting in low EMI and reliable paralleling, even when switching at very high frequency.



APT7F120B APT7F120S

Single die FREDFET



FEATURES

- **Fast switching with low EMI**
- **Low t_{rr} for high reliability**
- **Ultra low C_{rss} for improved noise immunity**
- **Low gate charge**
- **Avalanche energy rated**
- **RoHS compliant**

TYPICAL APPLICATIONS

- **ZVS phase shifted and other full bridge**
- **Half bridge**
- **PFC and other boost converter**
- **Buck converter**
- **Single and two switch forward**
- **Flyback**

Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
I_D	Continuous Drain Current @ T_C = 25°C	7	A
	Continuous Drain Current @ T_C = 100°C	5	
I_{DM}	Pulsed Drain Current ①	28	
V_{GS}	Gate-Source Voltage	±30	V
E_{AS}	Single Pulse Avalanche Energy ②	575	mJ
I_{AR}	Avalanche Current, Repetitive or Non-Repetitive	3	A

Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
P_D	Total Power Dissipation @ T_C = 25°C			335	W
$R_{\theta JC}$	Junction to Case Thermal Resistance			0.37	°C/W
$R_{\theta CS}$	Case to Sink Thermal Resistance, Flat, Greased Surface		0.11		
T_J,T_{STG}	Operating and Storage Junction Temperature Range	-55		150	°C
T_L	Soldering Temperature for 10 Seconds (1.6mm from case)			300	
W_T	Package Weight		0.22		oz
			6.2		g
Torque	Mounting Torque (TO-247 Package), 6-32 or M3 screw			10	in·lbf
				1.1	N·m

050-8144 Rev C 04-2009

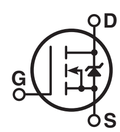
Static Characteristics T_J = 25°C unless otherwise specified

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit
$V_{BR(DSS)}$	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250µA		1200			V
$\Delta V_{BR(DSS)}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I_D = 250µA			1.41		V/°C
$R_{DS(on)}$	Drain-Source On Resistance ③	V_{GS} = 10V, I_D = 3A			1.57	2.4	Ω
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS} = V_{DS}$, I_D = 1mA		2.5	4	5	V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold Voltage Temperature Coefficient				-10		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 1200V	T_J = 25°C			250	µA
		V_{GS} = 0V	T_J = 125°C			1000	
I_{GSS}	Gate-Source Leakage Current	V_{GS} = ±30V				±100	nA

Dynamic Characteristics T_J = 25°C unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
g_{fs}	Forward Transconductance	V_{DS} = 50V, I_D = 3A		8		S
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 25V f = 1MHz		2565		pF
C_{rss}	Reverse Transfer Capacitance			31		
C_{oss}	Output Capacitance			190		
$C_{o(cr)}$ ④	Effective Output Capacitance, Charge Related	V_{GS} = 0V, V_{DS} = 0V to 800V		75		
$C_{o(er)}$ ⑤	Effective Output Capacitance, Energy Related			38		
Q_g	Total Gate Charge	V_{GS} = 0 to 10V, I_D = 3A, V_{DS} = 600V		80		nC
Q_{gs}	Gate-Source Charge			13		
Q_{gd}	Gate-Drain Charge			37		
$t_{d(on)}$	Turn-On Delay Time	**Resistive Switching** V_{DD} = 800V, I_D = 3A R_G = 4.7Ω⑥, V_{GG} = 15V		14		ns
t_r	Current Rise Time			8		
$t_{d(off)}$	Turn-Off Delay Time			45		
t_f	Current Fall Time			13		

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit
I_S	Continuous Source Current (Body Diode)	MOSFET symbol showing the integral reverse p-n junction diode (body diode) 				7	A
I_{SM}	Pulsed Source Current (Body Diode) ①					28	
V_{SD}	Diode Forward Voltage	I_{SD} = 3A, T_J = 25°C, V_{GS} = 0V				1.0	V
t_{rr}	Reverse Recovery Time	I_{SD} = 3A③ di_{SD}/dt = 100A/µs V_{DD} = 100V	T_J = 25°C			190	ns
			T_J = 125°C			325	
Q_{rr}	Reverse Recovery Charge		T_J = 25°C		0.64		µC
			T_J = 125°C		1.45		
I_{rrm}	Reverse Recovery Current		T_J = 25°C		7.5		A
			T_J = 125°C		10.7		
dv/dt	Peak Recovery dv/dt	I_{SD} ≤ 3A, di/dt ≤1000A/µs, V_{DD} = 800V, T_J = 125°C				25	V/ns

① Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

② Starting at T_J = 25°C, L = 127.78mH, R_G = 4.7Ω, I_{AS} = 3A.

③ Pulse test: Pulse Width < 380µs, duty cycle < 2%.

④ $C_{o(cr)}$ is defined as a fixed capacitance with the same stored charge as C_{OSS} with V_{DS} = 67% of $V_{(BR)DSS}$.

⑤ $C_{o(er)}$ is defined as a fixed capacitance with the same stored energy as C_{OSS} with V_{DS} = 67% of $V_{(BR)DSS}$. To calculate $C_{o(er)}$ for any value of V_{DS} less than $V_{(BR)DSS,}$ use this equation: $C_{o(er)}$ = -1.17E-7/V_{DS}^2 + 1.42E-8/V_{DS} + 2.01E-11.

⑥ R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

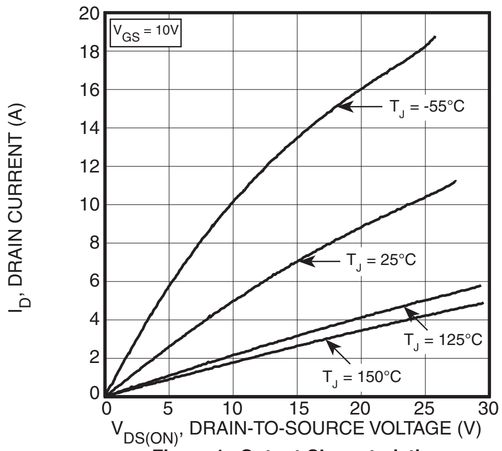


Figure 1, Output Characteristics

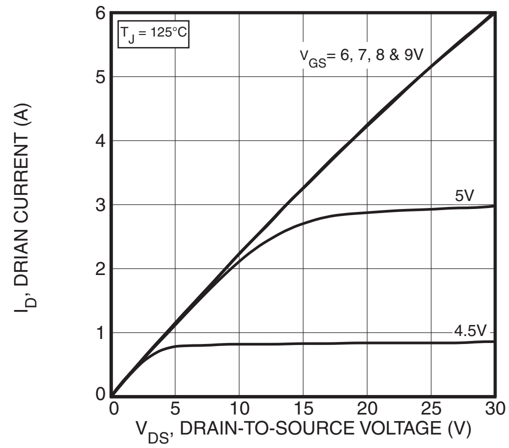


Figure 2, Output Characteristics

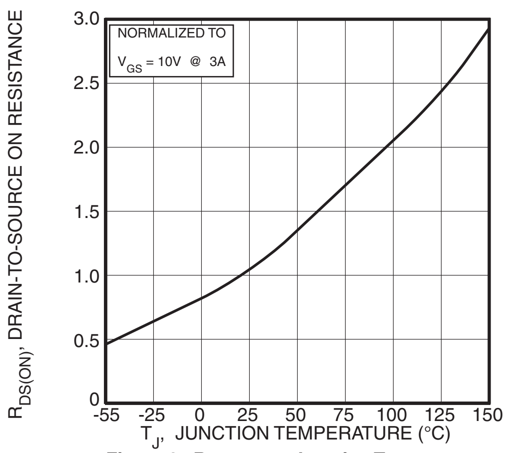


Figure 3, $R_{DS(ON)}$ vs Junction Temperature

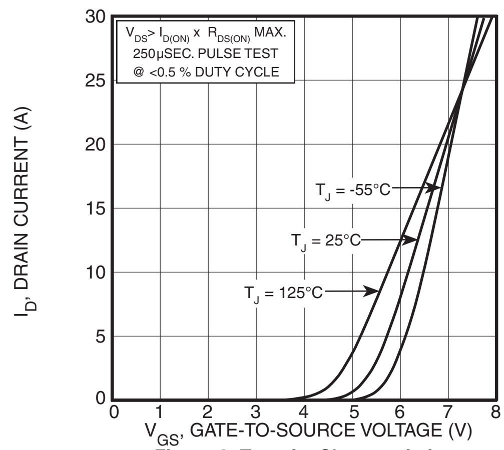


Figure 4, Transfer Characteristics

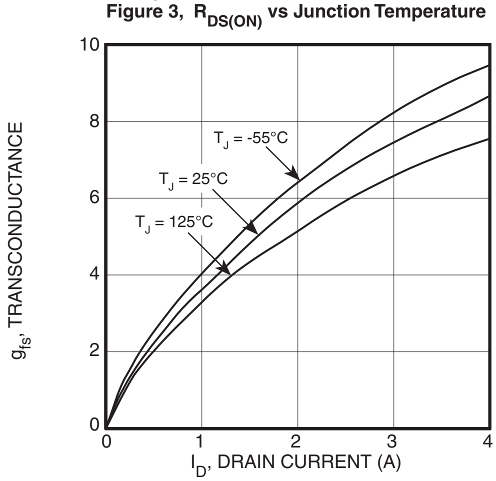


Figure 5, Gain vs Drain Current

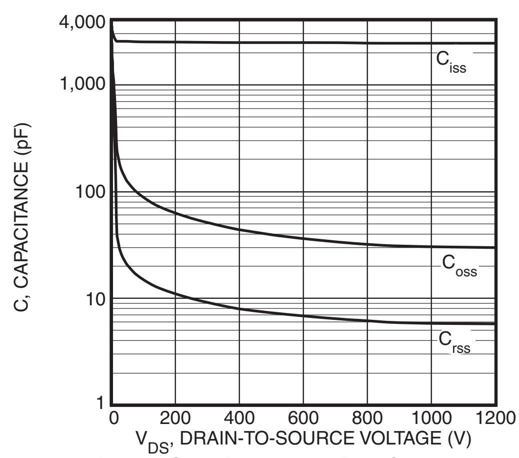


Figure 6, Capacitance vs Drain-to-Source Voltage

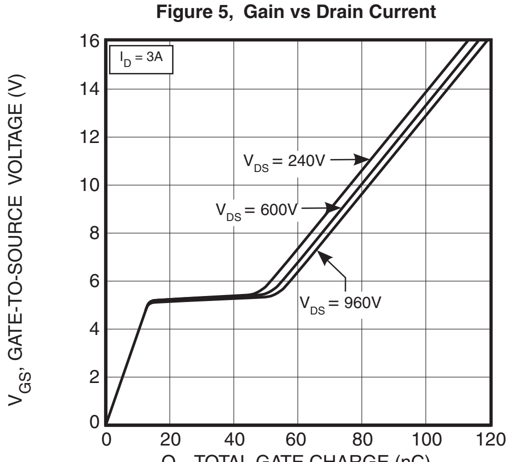


Figure 7, Gate Charge vs Gate-to-Source Voltage

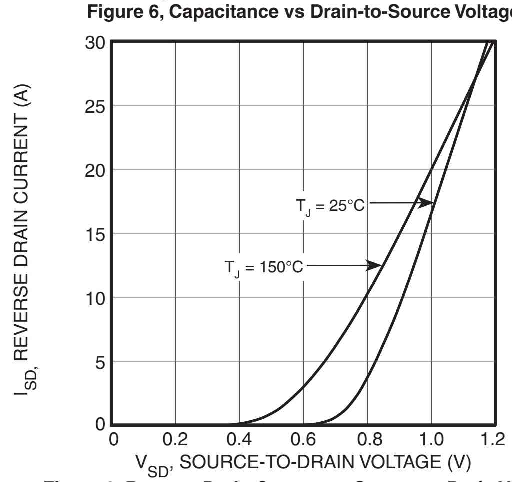


Figure 8, Reverse Drain Current vs Source-to-Drain Voltage

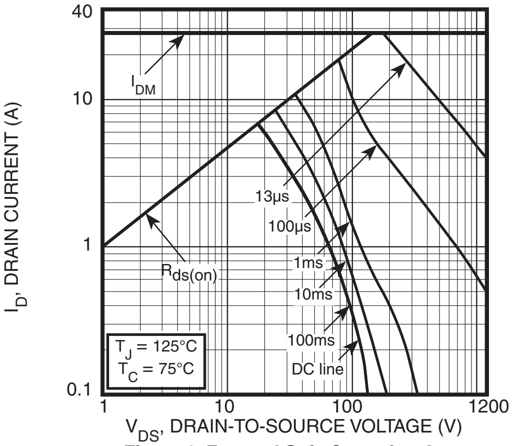


Figure 9, Forward Safe Operating Area

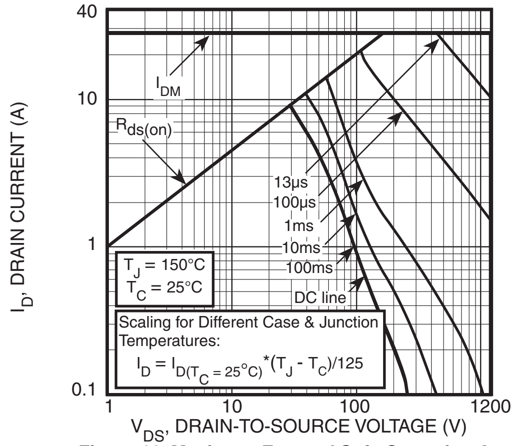


Figure 10, Maximum Forward Safe Operating Area

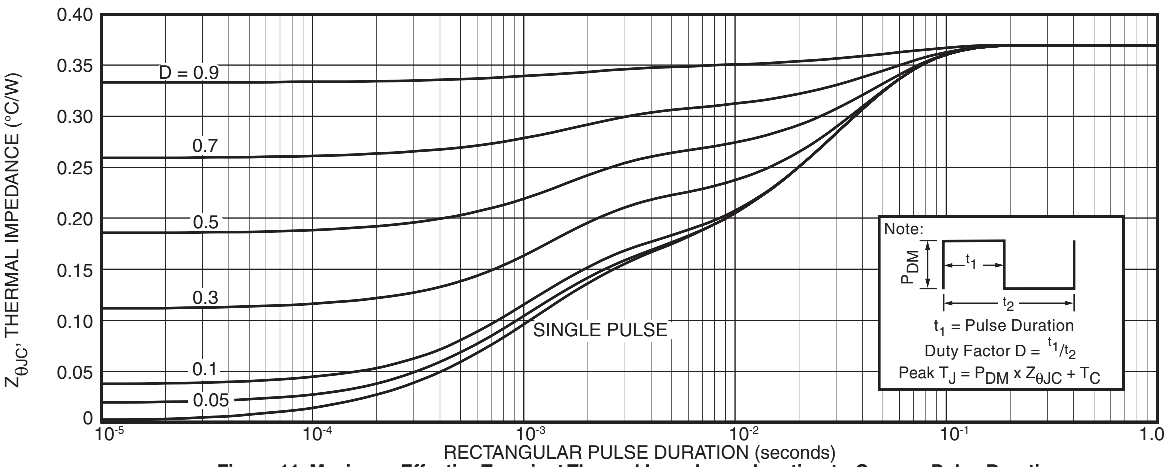
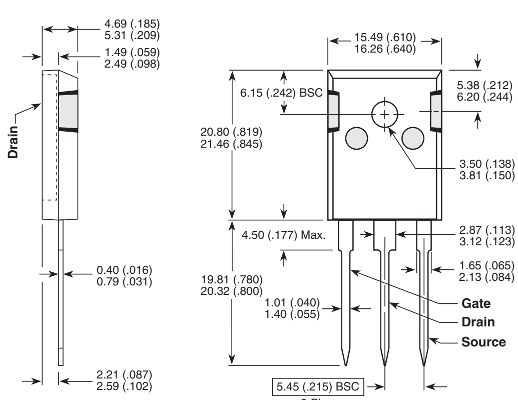


Figure 11. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration

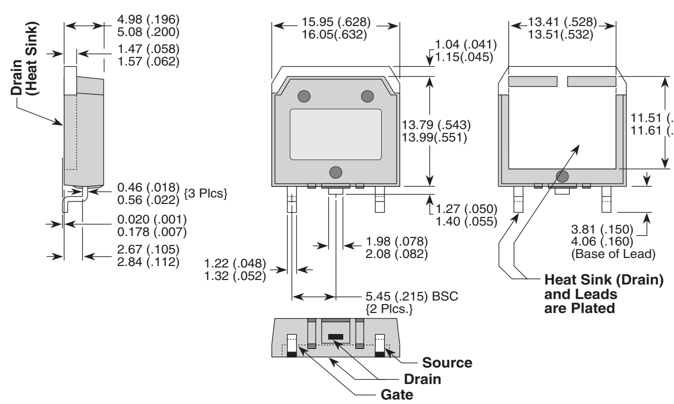
TO-247 (B) Package Outline

D^3PAK Package Outline

(e3) 100% Sn Plated



Dimensions in Millimeters and (Inches)



Dimensions in Millimeters (Inches)

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- Поставка сложных, дефицитных, либо снятых с производства позиций;
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- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.

Как с нами связаться

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